



STN3NE06L

N - CHANNEL 60V - 0.10 Ω - 3A - SOT-223 STripFET™ POWER MOSFET

PRELIMINARY DATA

TYPE	V _{DSS}	R _{DS(on)}	I _D
STN3NE06L	60 V	< 0.120 Ω	3 A

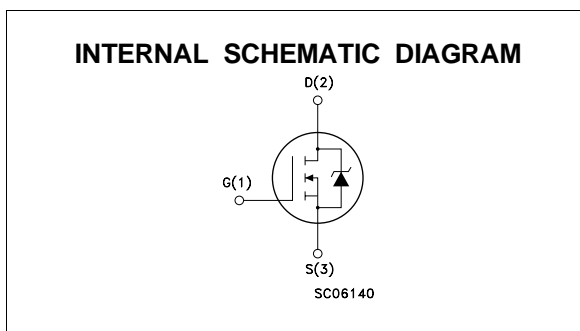
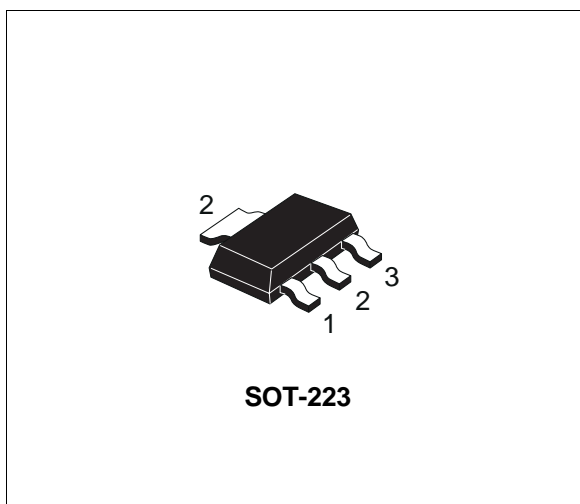
- TYPICAL R_{DS(on)} = 0.10 Ω
- EXCEPTIONAL dv/dt CAPABILITY
- AVALANCHE RUGGED TECHNOLOGY
- 100 % AVALANCHE TESTED
- APPLICATION ORIENTED CHARACTERIZATION

DESCRIPTION

This Power Mosfet is the latest development of STMicroelectronics unique "Single Feature Size™" stip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

APPLICATIONS

- DC MOTOR CONTROL (DISK DRIVES, etc.)
- DC-DC & DC-AC CONVERTERS
- SYNCHRONOUS RECTIFICATION



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	60	V
V _{DGR}	Drain- gate Voltage (R _{GS} = 20 k Ω)	60	V
V _{GS}	Gate-source Voltage	± 20	V
I _D	Drain Current (continuous) at T _c = 25 °C	3	A
I _D	Drain Current (continuous) at T _c = 100 °C	1.8	A
I _{DM} (*)	Drain Current (pulsed)	12	A
P _{tot}	Total Dissipation at T _c = 25 °C	2.5	W
	Derating Factor	0.02	W/°C
dv/dt(1)	Peak Diode Recovery voltage slope	6	V/ns
T _{stg}	Storage Temperature	-65 to 150	°C
T _j	Max. Operating Junction Temperature	150	°C

(*) Pulse width limited by safe operating area
New RDS (on) spec. starting from JULY 98

(1) I_{SD} \leq 12 A, di/dt \leq 200 A/ μ s, V_{DD} \leq V_{(BR)DSS}, T_j \leq T_{JMAX}

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THERMAL DATA

$R_{thj-pcb}$	Thermal Resistance Junction-PC Board	Max	50	$^{\circ}\text{C}/\text{W}$
$R_{thj-amb}$	Thermal Resistance Junction-ambient (Surface Mounted)	Max	60	$^{\circ}\text{C}/\text{W}$
T_l	Maximum Lead Temperature For Soldering Purpose		260	$^{\circ}\text{C}$

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max)	3	A
E_{AS}	Single Pulse Avalanche Energy (starting $T_j = 25^{\circ}\text{C}$, $I_D = I_{AR}$, $V_{DD} = 25\text{ V}$)	20	mJ

ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}\text{C}$ unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	$I_D = 250\ \mu\text{A}$ $V_{GS} = 0$	60			V
I_{DSS}	Zero Gate Voltage Drain Current ($V_{GS} = 0$)	$V_{DS} = \text{Max Rating}$ $V_{DS} = \text{Max Rating}$ $T_c = 125^{\circ}\text{C}$			1 10	μA μA
I_{GSS}	Gate-body Leakage Current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{ V}$			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ $I_D = 250\ \mu\text{A}$	1	1.7	2.5	V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS} = 10\text{ V}$ $I_D = 6\text{ A}$ $V_{GS} = 5\text{ V}$ $I_D = 6\text{ A}$		0.080 0.1	0.100 0.12	Ω Ω
$I_{D(on)}$	On State Drain Current	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $V_{GS} = 10\text{ V}$	3			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (*)	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $I_D = 1.5\text{ A}$	1	3		S
C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}$ $f = 1\text{ MHz}$ $V_{GS} = 0\text{ V}$		700	960	pF
C_{oss}	Output Capacitance			100	140	pF
C_{rss}	Reverse Transfer Capacitance			30	45	pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Time Rise Time	$V_{DD} = 30\text{ V}$ $I_D = 6\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 5\text{ V}$		17 35	23 50	ns ns
$(di/dt)_{on}$	Turn-on Current Slope	$V_{DD} = 25\text{ V}$ $I_D = 6\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		200		A/ μs
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 40\text{ V}$ $I_D = 12\text{ A}$ $V_{GS} = 5\text{ V}$		13 6 5	18	nC nC nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(voff)}$ t_f t_c	Off-voltage Rise Time Fall Time Cross-over Time	$V_{DD} = 48\text{ V}$ $I_D = 12\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 5\text{ V}$		9 18 30	12 25 45	ns ns ns

SOURCE DRAIN DIODE

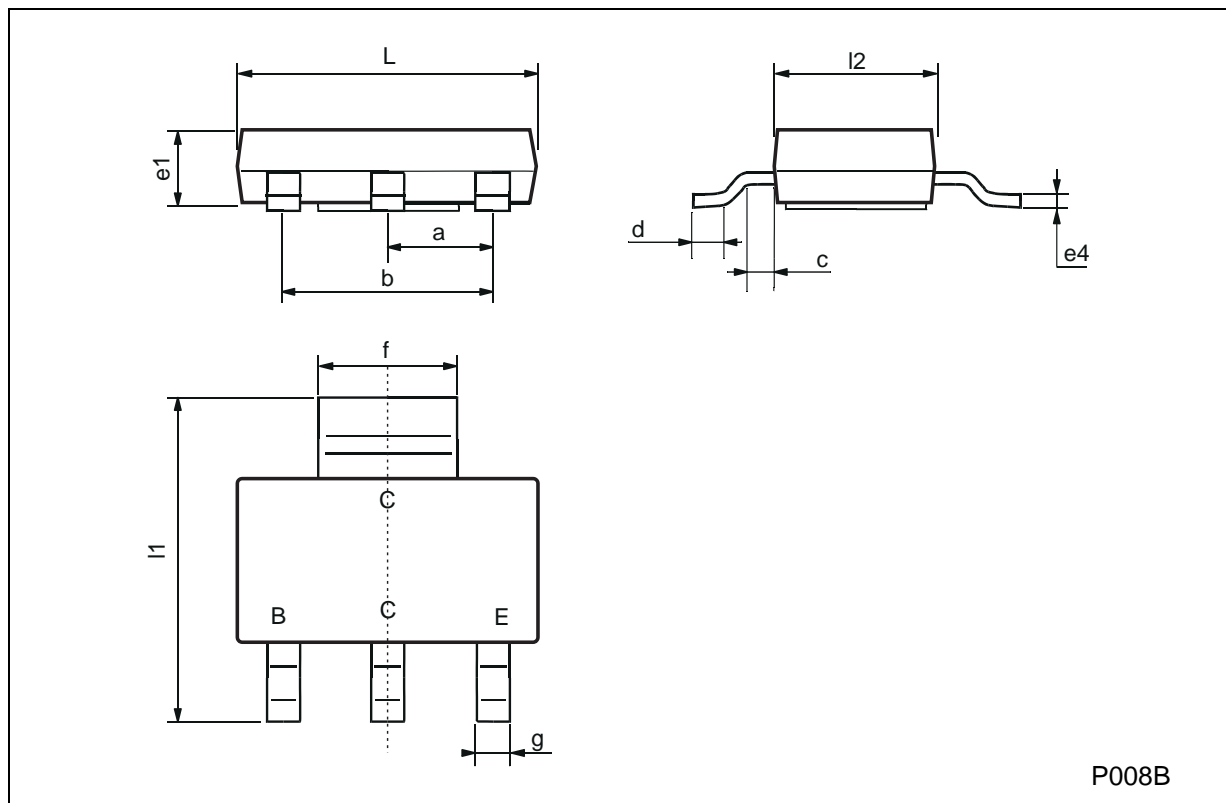
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM}(\bullet)$	Source-drain Current Source-drain Current (pulsed)				3 12	A A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 3\text{ A}$ $V_{GS} = 0$			1.5	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 12\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 25\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$		65 0.13 4		ns μC A

(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

(\bullet) Pulse width limited by safe operating area

SOT-223 MECHANICAL DATA

DIM.	mm			mils		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a	2.27	2.3	2.33	89.4	90.6	91.7
b	4.57	4.6	4.63	179.9	181.1	182.3
c	0.2	0.4	0.6	7.9	15.7	23.6
d	0.63	0.65	0.67	24.8	25.6	26.4
e1	1.5	1.6	1.7	59.1	63	66.9
e4			0.32			12.6
f	2.9	3	3.1	114.2	118.1	122.1
g	0.67	0.7	0.73	26.4	27.6	28.7
l1	6.7	7	7.3	263.8	275.6	287.4
l2	3.5	3.5	3.7	137.8	137.8	145.7
L	6.3	6.5	6.7	248	255.9	263.8



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